

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1 through 13 (canceled)

Claim 14 (new): An impurity introducing method which comprising:

a set of introducing an impurity selected from a group consisting of B, As, P, Sb and In into a surface of a semiconductor substrate; and

a step of radiating inactive plasma to the surface of the semiconductor substrate after the impurity introducing step.

Claim 15 (new): The impurity introducing method according to claim 14, wherein the step of radiating the plasma includes a step of radiating plasma such that the impurity possesses a desired impurity profile in the semiconductor substrate.

Claim 16 (new): The impurity introducing method according to claim 14, wherein the step of radiating the

plasma includes a step of radiating plasma which contains at least one kind of rare gas element.

Claim 17 (new): The impurity introducing method according to claim 16, wherein the step of radiating the plasma includes a step of radiating He plasma.

Claim 18 (new): The impurity introducing method according to claim 14, wherein the step of radiating the plasma includes a step of radiating plasma which contains hydrogen.

Claim 19 (new): The impurity introducing method according to claim 14, wherein the step of introducing the impurity includes a plasma-doping step.

Claim 20 (new): The impurity introducing method according to claim 14, wherein the step of introducing the impurity includes an ion-implanting step.

Claim 21 (new): The impurity introducing method according to claim 14, wherein the step of introducing the impurity includes a gas-doping step.

Claim 22 (new): A semiconductor device which is formed by using an impurity introducing method according to claim

14, wherein the semiconductor device is formed to have the impurity profile in which the impurity concentration at a depth position of 4nm is set to 1/10 or more of the impurity concentration on a surface of the semiconductor device.

Claim 23 (new): A semiconductor device according to claim 22, wherein the semiconductor device is formed to have the impurity profile in which the impurity concentration at a depth position of 7nm is set to 1/100 or more of the impurity concentration in the surface of the semiconductor device.